

(51) International Patent Classification:
H01L 21/3065 (2006.01)(21) International Application Number:
PCT/US2011/050379(22) International Filing Date:
2 September 2011 (02.09.2011)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
12/882,560 15 September 2010 (15.09.2010) US(71) Applicant (for all designated States except US): **LAM RESEARCH CORPORATION** [US/US]; 4650 Cushing Parkway, Fremont, CA 94538 (US).

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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(54) Title: METHODS FOR CONTROLLING PLASMA CONSTITUENT FLUX AND DEPOSITION DURING SEMICONDUCTOR FABRICATION AND APPARATUS FOR IMPLEMENTING THE SAME

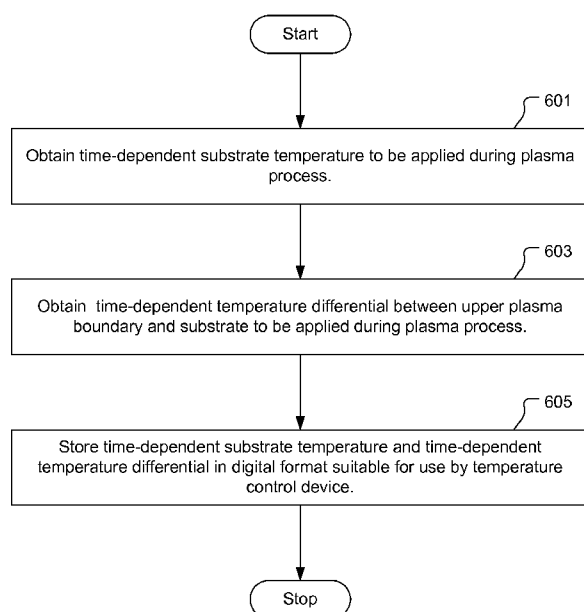


Fig. 6

(57) Abstract: A time-dependent substrate temperature to be applied during a plasma process is determined. The time-dependent substrate temperature at any given time is determined based on control of a sticking coefficient of a plasma constituent at the given time. A time-dependent temperature differential between an upper plasma boundary and a substrate to be applied during the plasma process is also determined. The time-dependent temperature differential at any given time is determined based on control of a flux of the plasma constituent directed toward the substrate at the given time. The time-dependent substrate temperature and time-dependent temperature differential are stored in a digital format suitable for use by a temperature control device defined and connected to direct temperature control of the upper plasma boundary and the substrate. A system is also provided for implementing upper plasma boundary and substrate temperature control during the plasma process.



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